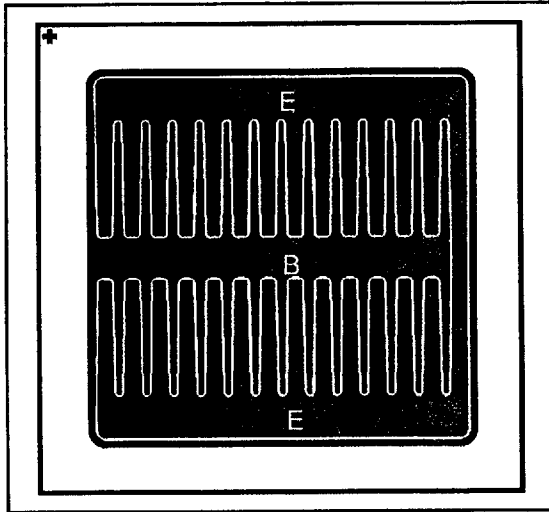


# PNP Power Switching Transistor Die

## Type OTC2670 100V, 30A

T-37-17



**Note:** Both Emitters must be connected to achieve design characteristics. Two 7 mil wires on each side suggested.

### Applications

- High inductance loads as used for solenoids
- Power inverters and switching regulators through 50 KHz.

### Features

- Contact Metallization  
Base and Emitter: Aluminum  
Collector: Alloy Gold Suitable for Eutectic Mount
- Complementary NPN Die: OTC2470-90L for PNP OTC2670-100H
- Dimensions:  
Die Size: .250 x .250 x .010 inch  
Emitter Bond Area (E): .185 x .020 inch  
Base Bond Area (B): .185 x .020 inch

### Electrical Characteristics At 25°C

| Symbol   | Parameter                            | 2670-100H |      | 2670-100L |      | Units | Test Conditions                         |
|----------|--------------------------------------|-----------|------|-----------|------|-------|-----------------------------------------|
|          |                                      | Min       | Max  | Min       | Max  |       |                                         |
| ICEX     | Collector Cutoff                     |           | -50  |           | -50  | μA    | VCE = -130, VBE = +0.5V                 |
| ICEX     | Collector Cutoff <sup>(2)</sup>      |           | -50  |           | -50  | mA    | VCE = -130, VBE = +0.5V, to 150°C       |
| IEBO     | Emitter Cutoff                       |           | -50  |           | -50  | μA    | VEB = -8V                               |
| VEBO     | Emitter-Base                         | -5.0      |      | -5.0      |      | V     | IC = -0.5mA                             |
| BVCBO    | Collector-Base                       | -130      |      | -160      |      | Vdc   | IC = -10mA                              |
| BVCEO    | Collector-Emitter <sup>(1)(2)</sup>  | -100      |      | -100      |      | Vdc   | IC = -100mA                             |
| BVCEO    | Collector-Emitter <sup>(1)</sup>     | -100      |      | -100      |      | V     | IC = -30mA                              |
| hFE      | D.C. Current Gain <sup>(1)</sup>     | 35        |      | 15        | 45   |       | IC = -5A, VCE = -2V                     |
| hFE      | D.C. Current Gain <sup>(1)(2)</sup>  | 30        | 90   | 15        | 45   |       | IC = -10A, VCE = -2V                    |
| hFE      | D.C. Current Gain <sup>(1)(2)</sup>  | 20        |      | 10        |      |       | IC = -20A, VCE = -2V                    |
| hFE      | D.C. Current Gain <sup>(1)(2)</sup>  | 10        |      | 5         |      |       | IC = -30A, VCE = -2V                    |
| VBE(SAT) | Base Saturation <sup>(1)(2)</sup>    |           | -1.8 |           | -1.8 | Vdc   | IC = -20A, IB = -3V                     |
| VCE(SAT) | Collector Saturation (1)(2)          |           | -0.8 |           | -0.8 | Vdc   | IC = -10A, IB = -1.0A                   |
| VCE(SAT) | Collector Saturation (1)(2)          |           | -1.8 |           | -1.8 | Vdc   | IC = -20A, IB = -3A                     |
| Ton      | Turn-on Time td + tr <sup>(2)</sup>  |           | 0.5  |           | 0.5  | μsec  | VC = -20V, IC = -10A, IB1 = IB2 = -0.5A |
| Toff     | Turn-off Time ts + tf <sup>(2)</sup> |           | 1.5  |           | 1.5  | μsec  | VC = -20V, IC = -10A, IB1 = IB2 = -0.5A |
| COB      | Output Capacitance <sup>(3)</sup>    |           | 750  |           | 750  | pf    | VCB = -10V, f = 1MHz                    |

(1) Pulse width 300 μsec 2% duty cycle

(2) Parameters verified on assembled devices. Data available upon request

(3) This parameter is guaranteed by design.

(4) The OTC2670-100L is used by Optek for device types 2N5738 and 2N5745, OTC2670-100H for types 2N5678, 2N5742 and 2N5853

Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

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